

Silicon NPN Power Transistors

2SD850

DESCRIPTION

www.datasheet4u.com

- With TO-3 package
- High voltage ,high speed

APPLICATIONS

- Line-operated horizontal deflection output applications

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

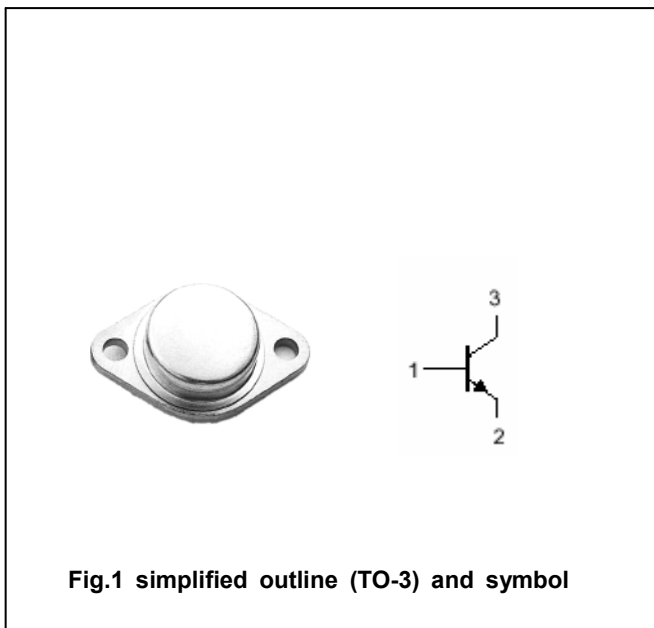


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	700	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		3	A
I _{CM}	Collector current-peak		5	A
P _T	Total power dissipation	T _C =90□	25	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-65~150	□

Silicon NPN Power Transistors

2SD850

CHARACTERISTICS

T_j=25°C unless otherwise specified

www.datasheet4u.com

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =0.1A; I _B =0	600			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10mA; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =2.5 A; I _B =0.8A			4.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =2.5 A; I _B =0.8A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =750V; I _E =0			50	μA
		V _{CB} =1500V; I _E =0			1.0	mA
h _{FE-1}	DC current gain	I _C =0.5A ; V _{CE} =5V	8			
h _{FE-2}	DC current gain	I _C =2.5A ; V _{CE} =10V	4		15	
t _f	Fall time	I _C =2.5A; I _{Bend} =0.8A; L _B =5μH			1.0	μs
t _s	Storage time			13		μs

PACKAGE OUTLINE

www.datasheet4u.com

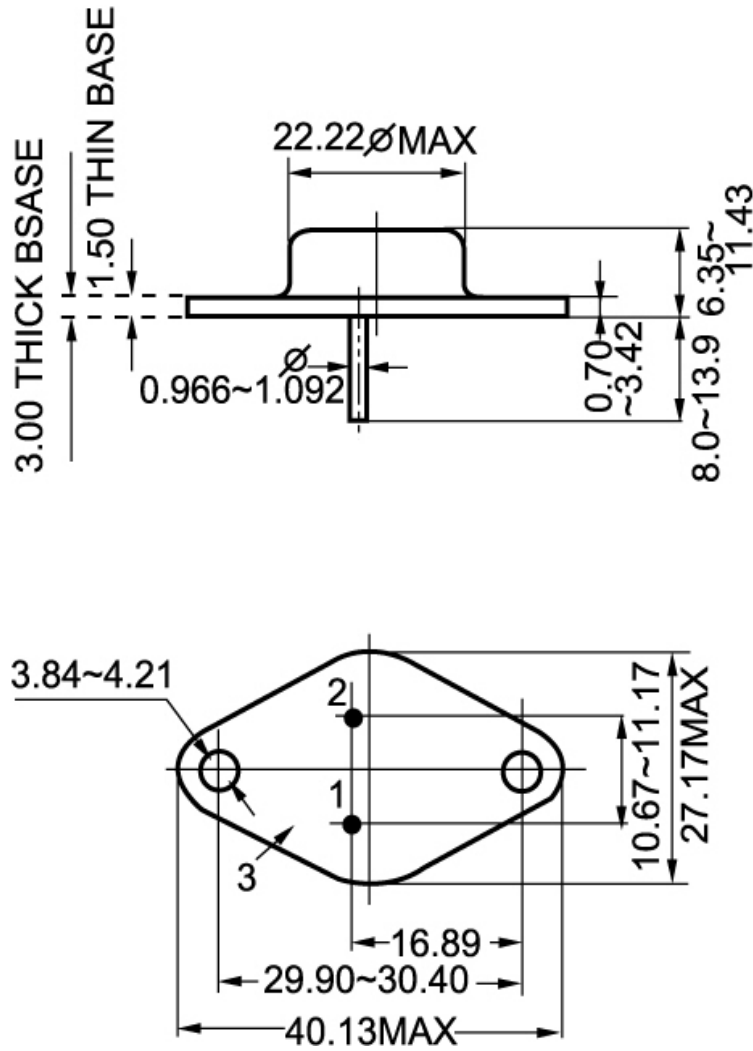


Fig.2 Outline dimensions